NCE Automotive N-Channel Super Trench Power MOSFET

Description

The NCEAP60T12AK uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

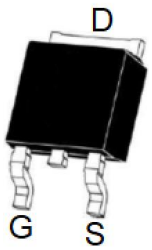
Application

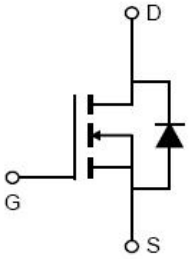
- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =60V,I_D =150A
  $R_{DS(ON)}$ < 4.3mΩ @ V_{GS}=10V (Typ:3.5mΩ)
  $R_{DS(ON)}$ < 5.3mΩ @ V_{GS}=4.5V (Typ:4.0mΩ)
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100% ΔVds tested
- **AEC-Q101 qualified**

TO-252-2L





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP60T12AK	NCEAP60T12AK	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	150	A
	I_D (100℃)	106	A
Pulsed Drain Current	I_{DM}	480	A
Maximum Power Dissipation	P_D	180	W
Derating factor		1.2	W/℃
Single pulse avalanche energy (Note 2)	E_{AS}	500	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	0.83	℃/W
Thermal Resistance,Junction-to-Ambient (Note 4)	$R_{\theta JA}$	60	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.0	1.7	2.4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	3.5	4.3	mΩ
		V_{GS}=4.5V, I_D=20A	-	4.0	5.3	mΩ
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=20A	40	-	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=30V,V_{GS}=0V, F=1.0MHz	-	4000	-	pF
Output Capacitance	C_{oss}		-	680	-	pF
Reverse Transfer Capacitance	C_{rss}		-	23	-	pF
Switching Characteristics (Note 1)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V,I_D=20A V_{GS}=10V,R_G=4.7Ω	-	11	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	56	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=20A, V_{GS}=10V	-	67	-	nC
Gate-Source Charge	Q_{gs}		-	12	-	nC
Gate-Drain Charge	Q_{gd}		-	8.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=20A	-	-	1.2	V
Diode Forward Current	I_S		-	-	150	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = I_S di/dt = 100A/μs	-	48	-	nS
Reverse Recovery Charge	Qrr		-	60	-	nC

Notes:

1. Guaranteed by design, not subject to production
2. EAS condition : Tj=25℃,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25Ω
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175°C. The SOA curve provides a single pulse rating.
4. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

Typical Electrical and Thermal Characteristics

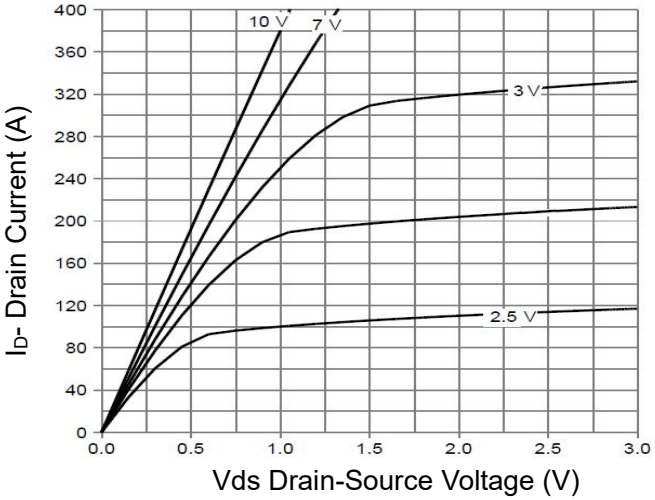


Figure 1 Output Characteristics

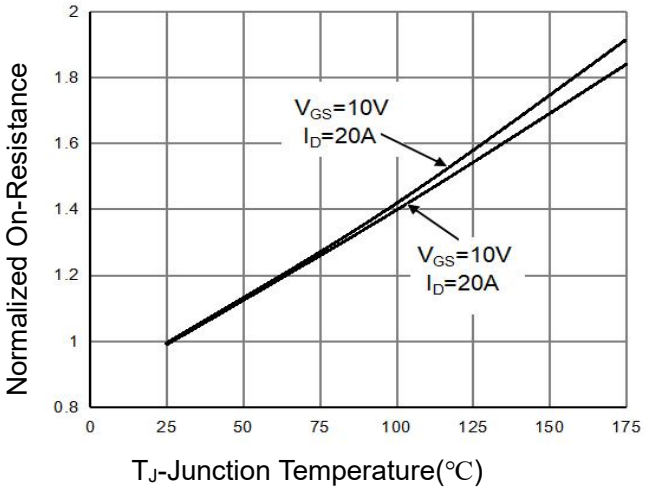


Figure 4 Rdson-JunctionTemperature

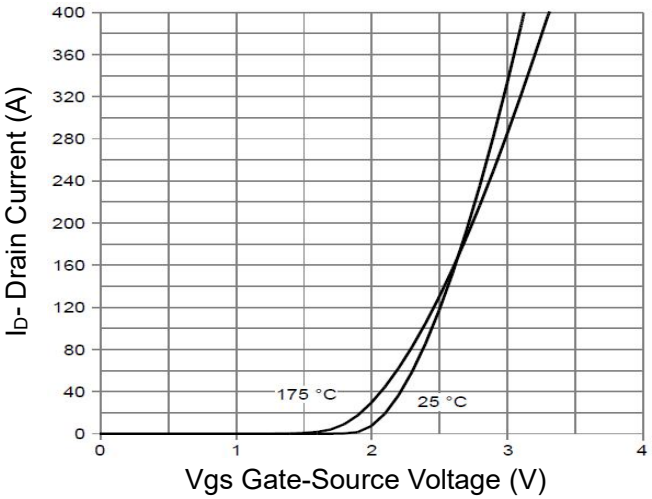


Figure 2 Transfer Characteristics

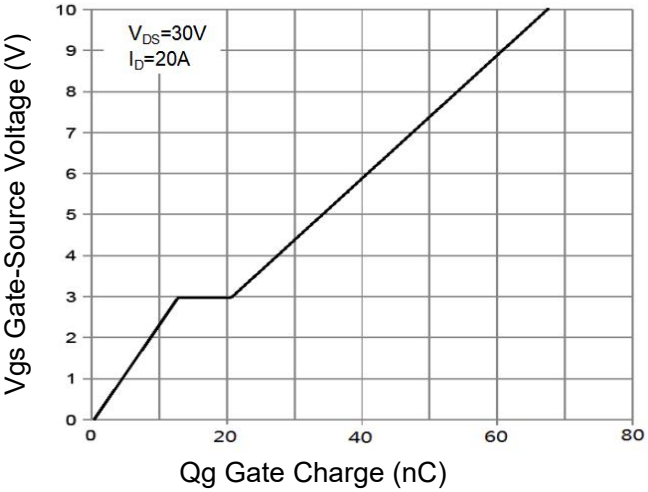


Figure 5 Gate Charge

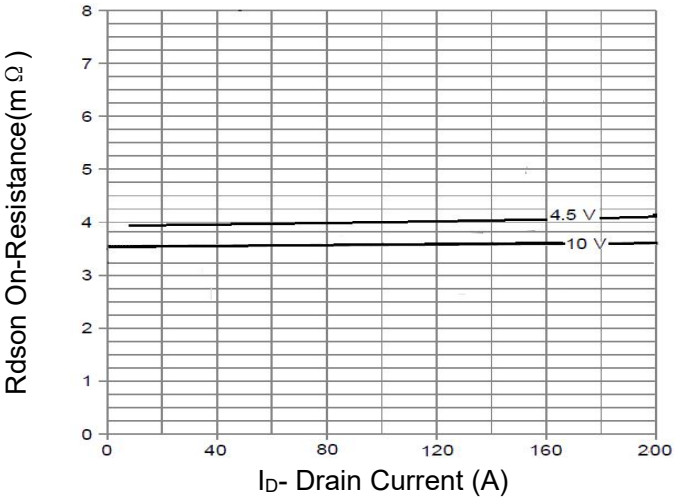


Figure 3 Rdson- Drain Current

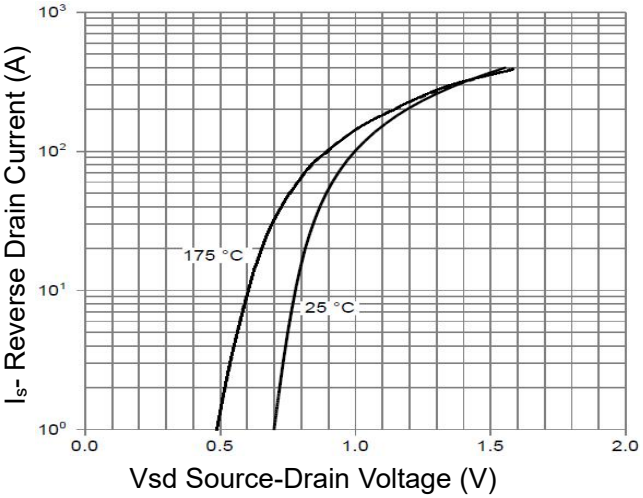


Figure 6 Source- Drain Diode Forw

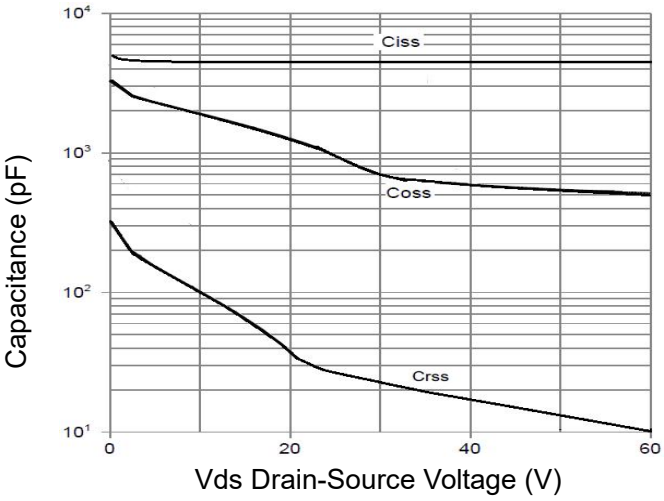


Figure 7 Capacitance vs Vds

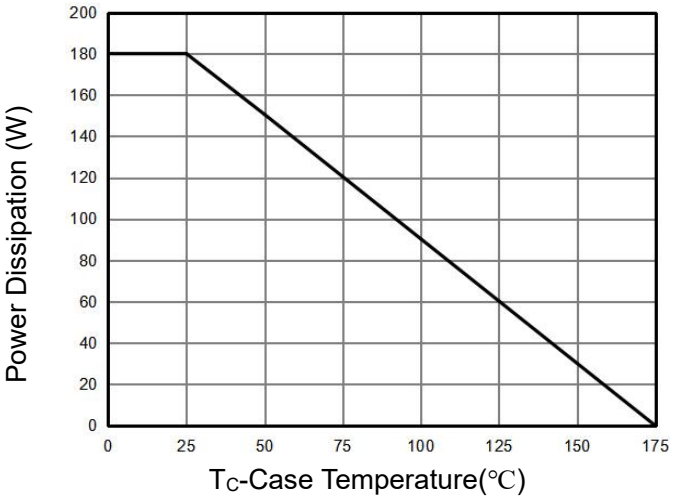


Figure 9 Power De-rating

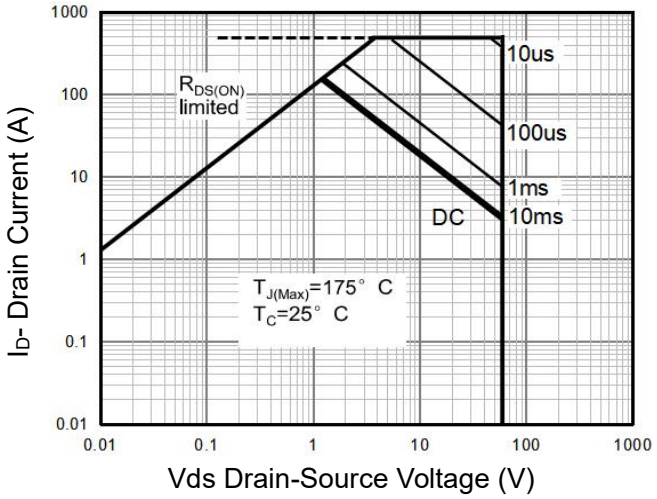


Figure 8 Safe Operation Area (Note 3)

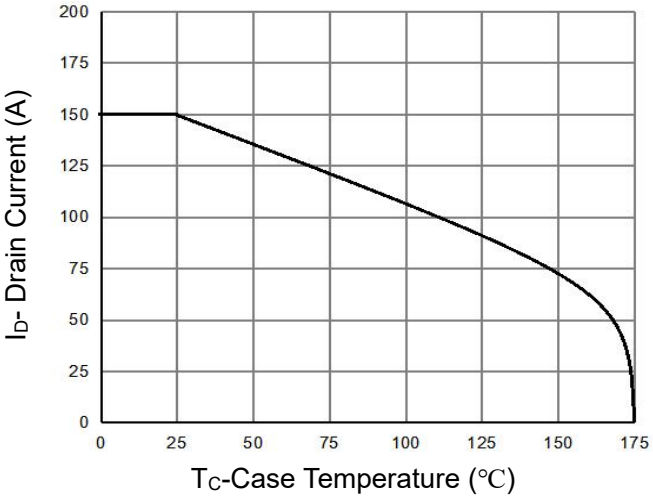


Figure 10 Current De-rating

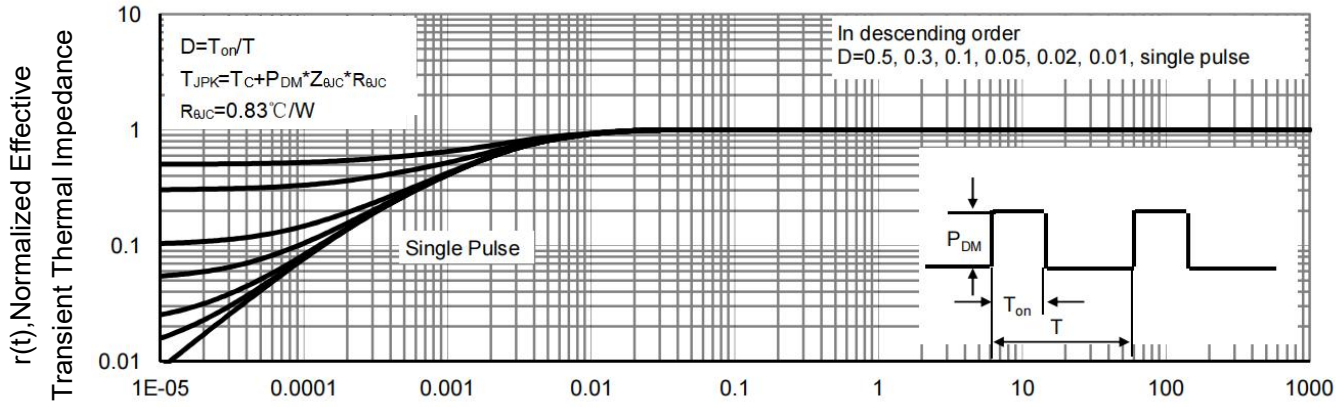
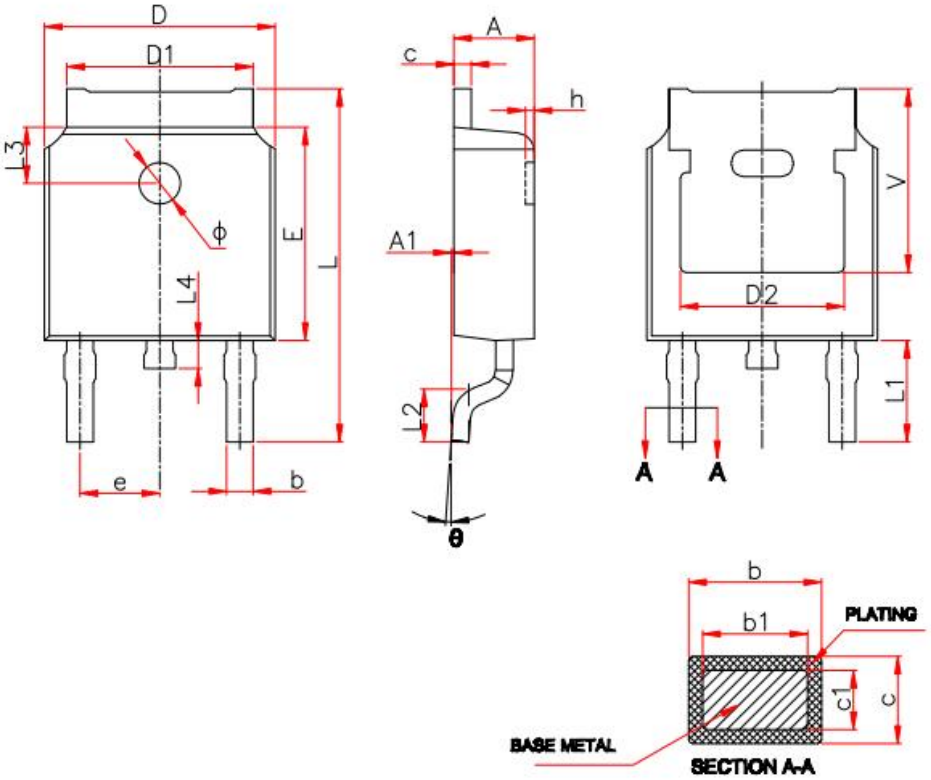


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-2L Package Information



Symbol	Millimeters	
	Min.	Max.
A	2.20	2.40
A1	0.00	0.13
b	0.66	0.86
b1	0.73	0.79
c	0.46	0.58
c1	0.50	0.52
D	6.50	6.70
D1	5.10	5.46
D2	4.83 REF.	
E	6.00	6.20
e	2.19	2.39
L	9.80	10.40
L1	2.90 REF.	
L2	1.40	1.70
L3	1.60 REF.	
L4	0.60	1.00
Φ	1.10	1.30
θ	0°	8°
h	0.00	0.30
V	5.35 REF.	

Revision History

Revision	Date	Subjects
V1.0	2023.02.12	Product data sheet
V2.0	2023.07.06	$R_{\theta JA}$

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